ON Semiconductor®

Final Product/Process Change Notification

Document # : FPCN22039X
Issue Date: 21 December 2017

Title of Change:	Qualification of ON Semiconductor Mountain Top, USA facility as an additional wafer fab location for MV5 Technology
Proposed first ship date:	28 March 2018
Contact information:	Contact your local ON Semiconductor Sales Office or Yuna Im <yuna.im@onsemi.com>
Samples:	Contact your local ON Semiconductor Sales Office
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or Youngchul Lee<youngchul.lee@onsemi.com>.
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <PCN.Support@onsemi.com>.
Change Part Identification:	Affected parts will be identified with a date code of WW07'18 or later
Change category:	☒ Wafer Fab Change ☐ Assembly Change ☐ Test Change ☐ Other _____

Change Sub-Category(s): *[Multiple options might be applicable]*

- ☒ Manufacturing Site Change/Addition
- ☐ Manufacturing Process Change
- ☐ Material Change
- ☐ Product specific change
- ☐ Datasheet/Product Doc change
- ☐ Shipping/Packaging/Marking
- ☐ Other: _____

Sites Affected:	ON Semiconductor Sites: ON Mountain Top, PA	External Foundry/Subcon Sites: None

Description and Purpose:

This is a Final Change Notification to inform customers of the qualification of ON Semiconductor Mountain Top, USA facility as an additional wafer fab location for MV5 Technology. Upon the expiration of this notification, all products listed here will be dual sourced from its current location, ON Semiconductor wafer fab in Bucheon, Korea.

	Before Change Description	After Change Description
Fab site	ON Bucheon, Korea	ON Bucheon, Korea ON Mountain Top, PA

Reliability Data Summary:

DEVICE NAME: FDB075N15A
PACKAGE: TO-263

Test	Specification	Condition	Interval	Results
PC	JEDS22 A113	Performed prior to TC, UHAST, HAST and IOL.		0/924
EV	JEDS22 B101	Device construction, marking, and workmanship		0/All
PV	Device specification	Tested to device specification requirements		0/45
HTRB	MILSTD750-1 method M1038A	Tj= 175C, bias= 120V, 1000 hrs	1000 hrs	0/231
HTGB	JESD22 A108	Ta= 175C, bias= 20V, 1000 hrs	1000 hrs	0/231
TC	JESD22 A104; Q101 appendix 6	T air= -65C to 150C, t dwell > 15 min, 500 cycles	500 cycles	0/231
UHAST	JESD22 A118	Ta= 130C, RH= 85%, no bias, 96 hrs	96 hrs	0/231
HAST	JESD22 A110	Ta= 130C, RH= 85%, bias= 42V, 96 hrs	96 hrs	0/231
IOL	MIL-STD-750 Method 1037	Ta=25C, delta Tj=100C, ton=toff=3.5min, 8572 cycles	8572 cycles	0/231
ESD	AEC Q101-001/005	Prefer CDM and HBM.		0/6
DPA	AEC Q101-004 Section 4	Post H3TRB or HAST and TC		0/39
RSH	JESD22 B106	Per AEC - Q101		0/30
WBS	MIL-STD-750 Method 2037	Pre & post process change		0/66
BS	AEC Q101-003			0/66
DS	MIL-STD-750 Method 2017			0/66
UIS	AEC Q101-004 Section 2			0/72

Electrical Characteristic Summary:

Electrical characteristics are not impacted.

List of Affected Parts:

Part Number	Qualification Vehicle
FDB075N15A	FDB075N15A
FDB0690N1507L	
FDP075N15A-F102	
FDPF190N15A	
PCFD075N15AW	